

Notice of References Cited		Application/Control No. 10/586,176	Applicant(s)/Patent Under Reexamination KOHLER ET AL.	
		Examiner FERNANDO N. HIDALGO	Art Unit 2827	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,909,635	06-2005	Forbes et al.	365/185.18
*	B	US-2004/0027877	02-2004	Kotz et al.	365/200
*	C	US-6,888,749	05-2005	Forbes, Leonard	365/185.01
	D	US-			
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	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Vuillaume et al., Charging and discharging properties of electron traps created by hot-carrier injections in gate oxide of n-channel metal oxide semiconductor field effect transistors, March 1993, J. Appl. Physics, Vol. 73, No. 5. Whole document pertinent.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.